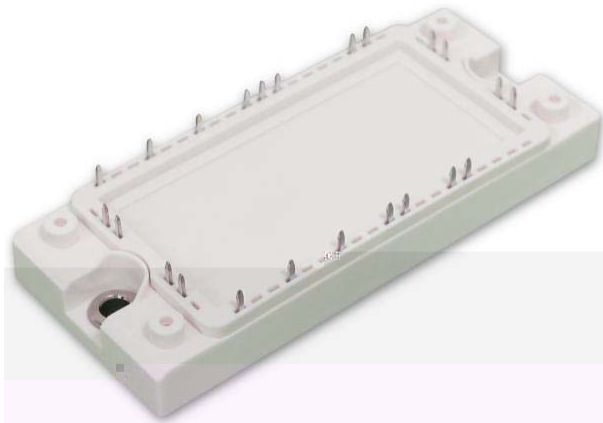




## IGBT Modules



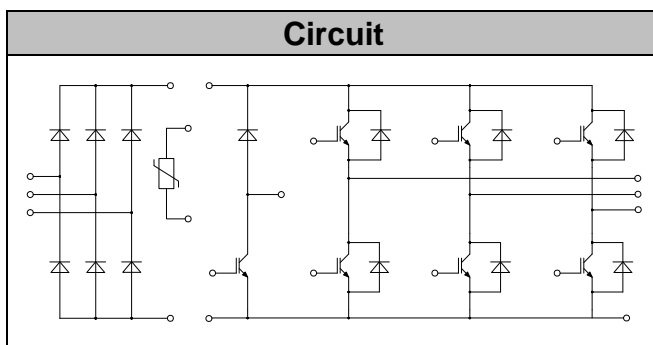
$V_{CES}$             1200V  
 $I_C$                  50A

## Applications

- Motor Drivers
- AC and DC servo drive amplifier
- UPS (Uninterruptible Power Supplies)

## Features

- Low switching losses
- Low  $V_{ce(sat)}$  with positive temperature coefficient
- Including fast & soft recovery anti-parallel FWD
- Low inductance case
- High short circuit capability(10us)
- Maximum junction temperature 175°C



### ● IGBT- inverter

#### Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	$V_{CES}$	$V_{GE}=0V, I_C=1mA, T_{vj}=25$	1200	V
Continuous Collector Current	$I_C$	$T_c=100, T_{vjmax}=175$	50	A
Repetitive Peak Collector Current	$I_{CRM}$	$tp=1ms$	100	A
Gate-Emitter Voltage	$V_{GES}$	$T_{vj}=25$	$\pm 20$	V
Total Power Dissipation	$P_{tot}$	$T_c=25$ $T_{vjmax}=175$	288	W



## ● IGBT- inverter

### Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=2.0mA, T_{vj}=25$	5.2	5.8	6.4	V
Collector-Emitter Cut-off Current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=50A, V_{GE}=15V, T_{vj}=25$		1.90	2.30	V
		$I_C=50A, V_{GE}=15V, T_{vj}=125$		2.30		
		$I_C=50A, V_{GE}=15V, T_{vj}=150$		2.40		
Gate Charge	$Q_G$			0.35		uC
Input Capacitance	$C_{ies}$	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz, T_{vj}=25^{\circ}C$		2.60		nF
Reverse Transfer Capacitance	$C_{res}$			0.10		nF
Gate-Emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25$			400	nA
Turn-on Delay Time	$t_{d(on)}$	$I_C=50A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=15\Omega$ $T_{vj}=25$		168		ns
Rise Time	$t_r$			34		ns
Turn-off Delay Time	$t_{d(off)}$			320		ns
Fall Time	$t_f$			78		ns
Energy Dissipation During Turn-on Time	$E_{on}$			5.42		mJ
Energy Dissipation During Turn-off Time	$E_{off}$			4.15		mJ
Turn-on Delay Time	$t_{d(on)}$	$I_C=50A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=15\Omega$ $T_{vj}=125$		175		ns
Rise Time	$t_r$			42		ns
Turn-off Delay Time	$t_{d(off)}$			426		ns
Fall Time	$t_f$			148		ns
Energy Dissipation During Turn-on Time	$E_{on}$			7.26		mJ
Energy Dissipation During Turn-off Time	$E_{off}$			5.80		mJ
SC Data	$I_{sc}$	$T_p \leq 10\mu s, V_{GE}=15V, T_{vj}=150$ , $V_{cc}=900V, V_{CEM} \leq 1200V$		260		A



# MG50P12E1A

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## ● IGBT-brake-chopper

### Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	$V_{CES}$	$V_{GE}=0V, I_C=1mA, T_{vj}=25$	1200	V
Continuous Collector Current	$I_C$	$T_c=100, T_{vjmax}=175$	35	A
Repetitive Peak Collector Current	$I_{CRM}$	$t_p=1ms$	70	A
Gate-Emitter Voltage	$V_{GES}$	$T_{vj}=25$	$\pm 20$	V
Total Power Dissipation	$P_{tot}$	$T_c=25$ $T_{vjmax}=175$	227	W

### Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=1.4mA, T_{vj}=25$	5.2	6.0	6.8	V



Turn-on Delay Time	$t_{d(on)}$	$I_C = 35\text{ A}$ $V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_G = 12\Omega$ $T_{vj} = 125$	38	ns
Rise Time	$t_r$		21	ns
Turn-off Delay Time	$t_{d(off)}$		178	ns
Fall Time	$t_f$		170	ns
Energy Dissipation During Turn-on Time	$E_{on}$		2.90	mJ
Energy Dissipation During Turn-off Time	$E_{off}$		2.90	mJ
SC Data	$I_{sc}$		$T_p \leq 10\mu s, V_{GE} = 15\text{ V}, T_{vj} = 150$ , $V_{cc} = 900\text{ V}, V_{CEM} \leq 1200\text{ V}$	150

## ● Diode-Brake-Chopper

### Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_j = 25$	1200	V
Continuous DC Forward Current	$I_F$		15	A
Repetitive Peak Forward Current	$I_{FRM}$	$t_p = 1\text{ ms}$	30	A
$I^2t$ -value	$I^2t$	$V_R = 0, t_p = 10\text{ ms}, T_j = 125$	48.0	A <sup>2</sup> s
		$V_R = 0, t_p = 10\text{ ms}, T_j = 150$	42.0	

### Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	$V_F$	$I_F = 15\text{ A}, T_{vj} = 25$		1.95		V
		$I_F = 15\text{ A}, T_{vj} = 125$		1.80		
		$I_F = 15\text{ A}, T_{vj} = 150$		1.70		
Recovered Charge	$Q_{rr}$	$I_F = 15\text{ A}$		1.10		uC
Peak Reverse Recovery Current	$I_{rr}$	$V_R = 600\text{ V}$ $-di_F/dt = 550\text{ A}/\mu s$		12.0		A
Reverse Recovery Energy	$E_{rec}$	$T_{vj} = 25$		0.30		mJ
Recovered Charge	$Q_{rr}$	$I_F = 15\text{ A}$		1.90		uC
Peak Reverse Recovery Current	$I_{rr}$	$V_R = 600\text{ V}$ $-di_F/dt = 550\text{ A}/\mu s$		14.0		A
Reverse Recovery Energy	$E_{rec}$	$T_{vj} = 125$		0.60		mJ



## ● Diode-Rectifier

### Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	$T_j=25$	1600	V
Average output Current 50/60Hz, sine wave	$I_{F(AV)}$	$T_c=100$	50	A
Maximum RMS Current at Rectifier Output	$I_{RMSM}$	$T_c=100$	100	A
Surge Forward Current	$I_{FSM}$	$V_R=0, t_p=10ms, T_j=45$	525	A
$I^2t$ -value	$I^2t$	$V_R=0, t_p=10ms, T_j=45$	1378	A <sup>2</sup> s

### Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Diode Forward Voltage	$V_F$	$I_F=50A, T_j=125$		1.0		V
Reverse Current	$I_R$	$T_j=125, V_R=1600V$			1.5	mA

## ● NTC-Thermistor

### Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Rated Resistance	$R_{25}$			5.0		k
Deviation of R100	$\Delta R/R$	$T_c=100, R_{100}=493.3$	-5		5	%
Power Dissipation	$P_{25}$				20.0	mW
B-value	$B_{25/50}$	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15 K))]$		3375		K



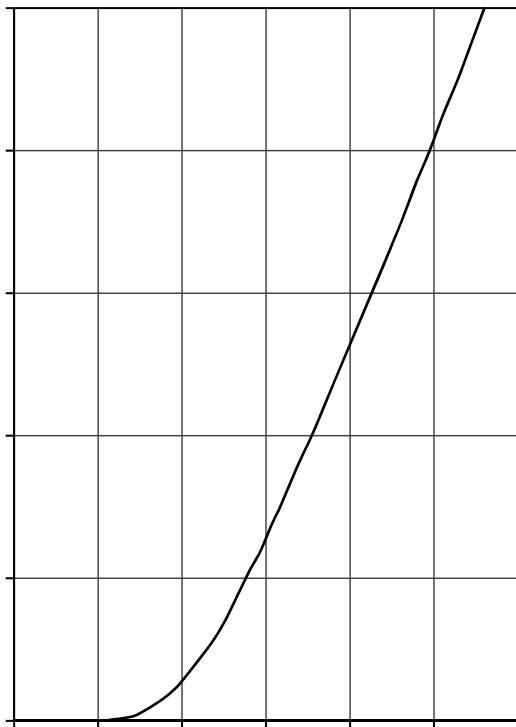
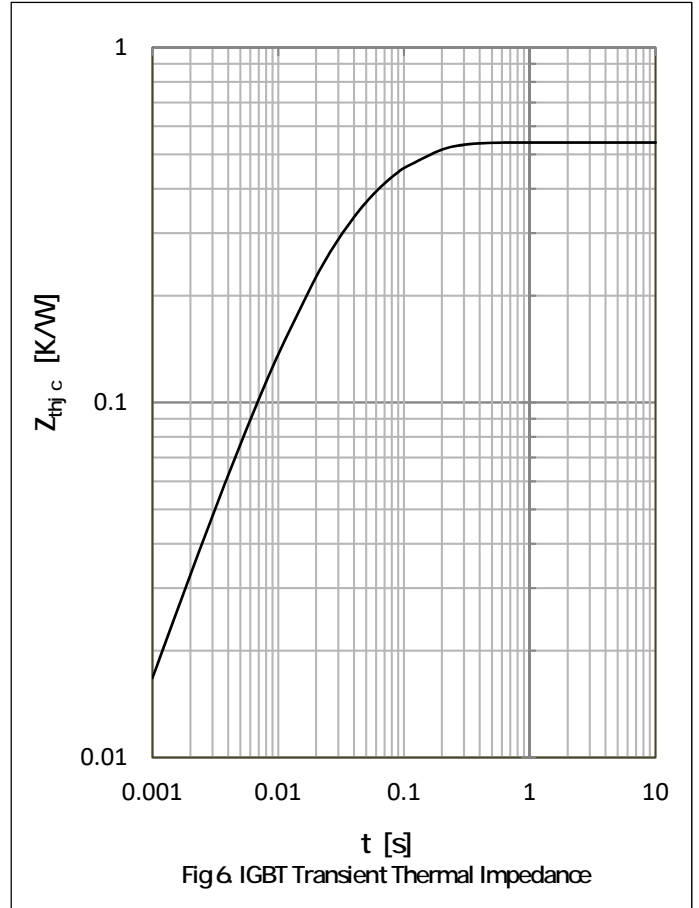
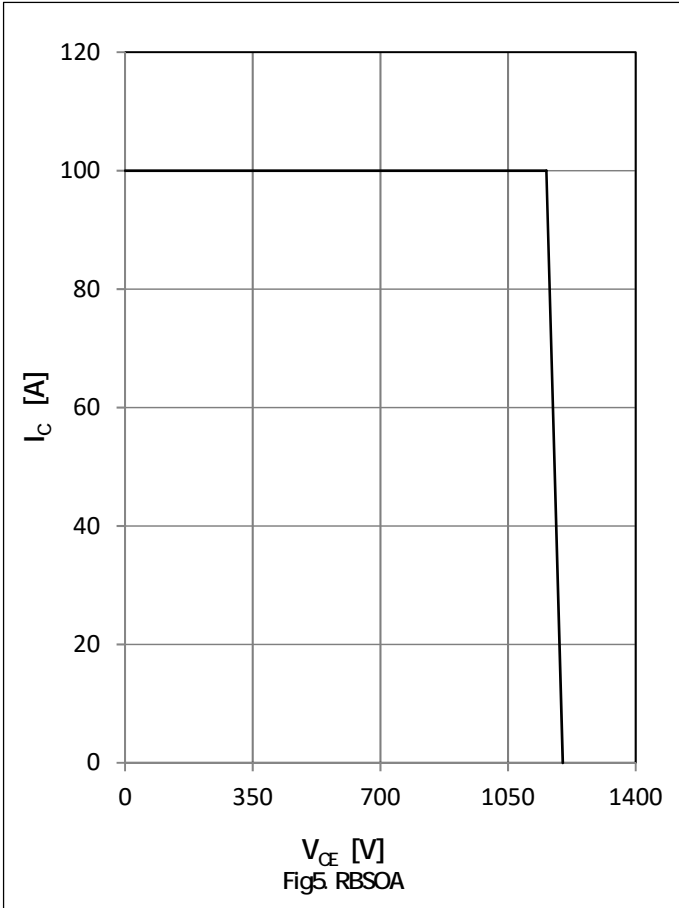
## ● Module Characteristics

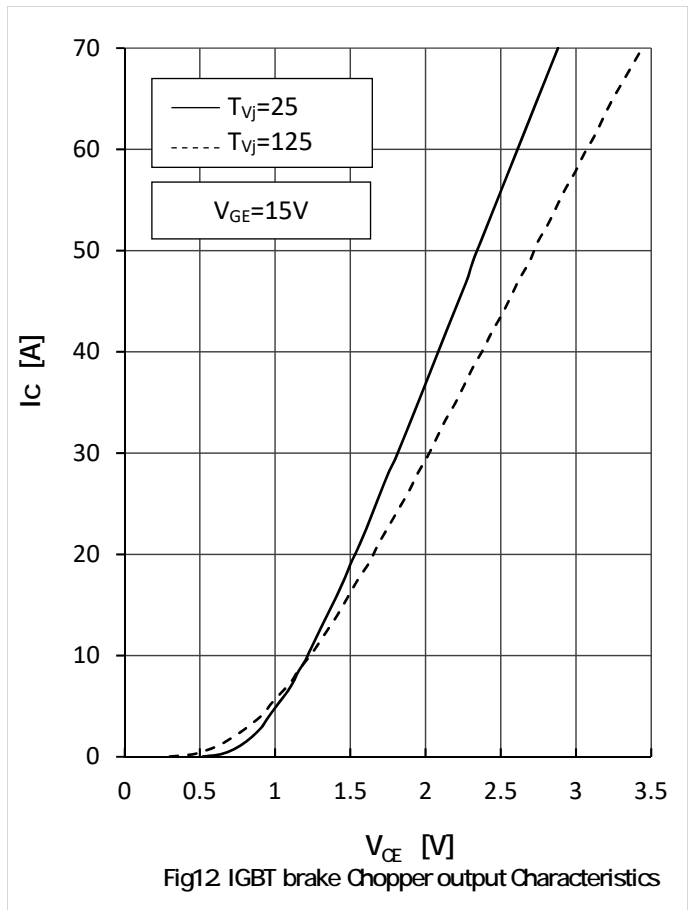
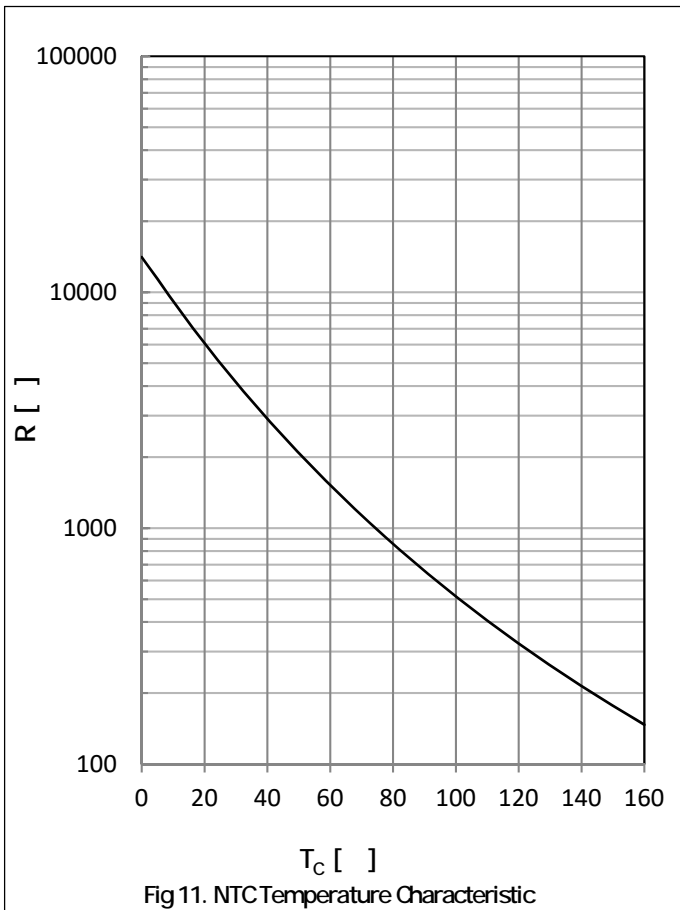
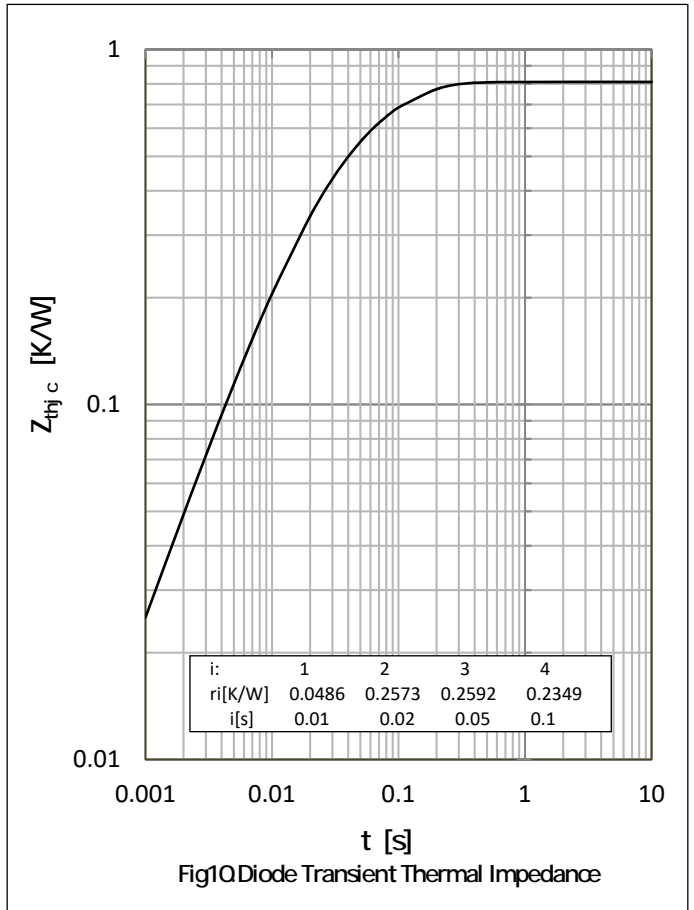
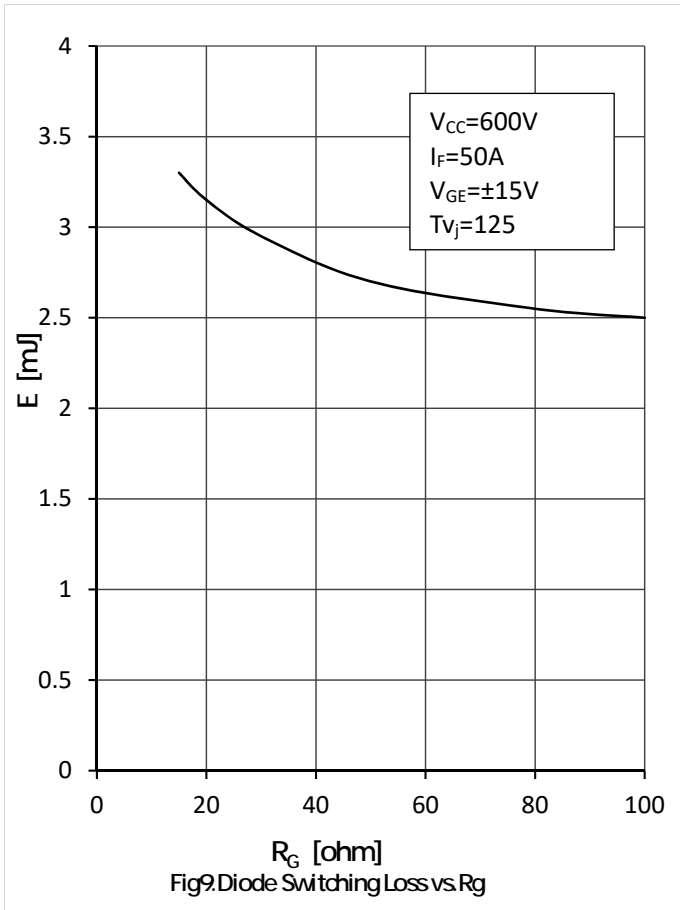
$T_C=25^{\circ}\text{C}$  unless otherwise specified

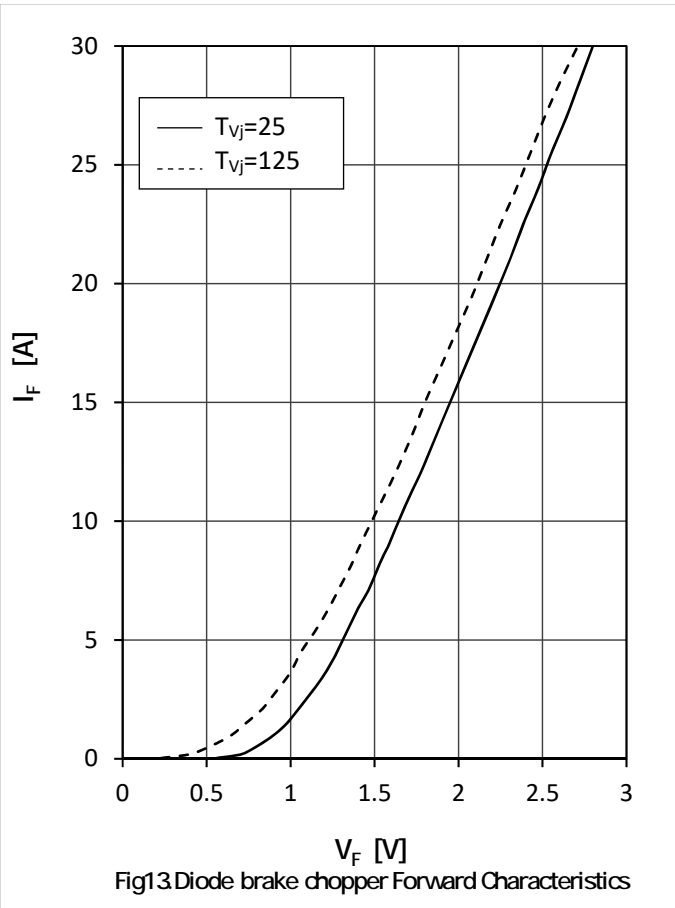
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation voltage	$V_{\text{isol}}$	$t=1\text{min}, f=50\text{Hz}$	2500			V
Maximum Junction Temperature	$T_{\text{jmax}}$				175	
Operating Junction Temperature	$T_{\text{vjop}}$		-40		150	
Storage Temperature	$T_{\text{stg}}$		-40		125	
Stray-inductance-module	$L_{\text{SCE}}$			60		nH
Module lead resistance, terminals-chip	$R_{\text{CC'+EE'}}$	$T_C=25^{\circ}\text{C}$ , per switch		4.0		m
	$R_{\text{AA'+CC'}}$			3.0		
Thermal Resistance Junction-to Case	$R_{\text{JC}}$	per IGBT-inverter			0.52	K/W
		per Diode-inverter			0.81	
		per IGBT-brake-copper			0.66	
		per Diode-chopper			1.50	
		per Diode-rectifier			0.75	
Thermal Resistance Case-to Sink	$R_{\text{CS}}$	per IGBT-inverter		0.31		K/W
		per Diode-inverter		0.48		
		per IGBT-brake-copper		0.33		
		per Diode-chopper		0.70		
		per Diode-rectifier		0.36		
		per Module		0.02		
Mounting Force Per Clamp	F		3.0		6.0	N
Weight of Module	G			180		g





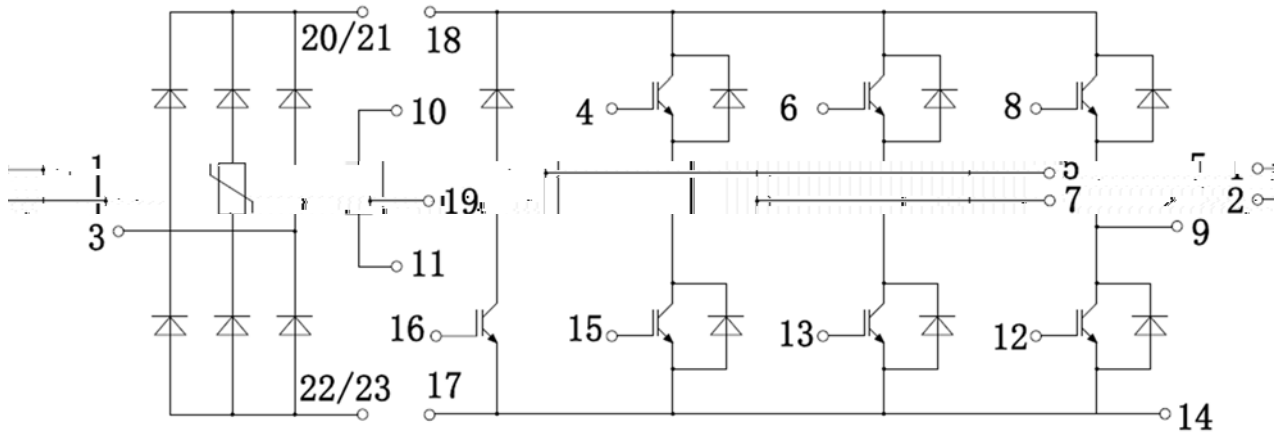









## ● Circuit Diagram



## ● Package Outline Information

